

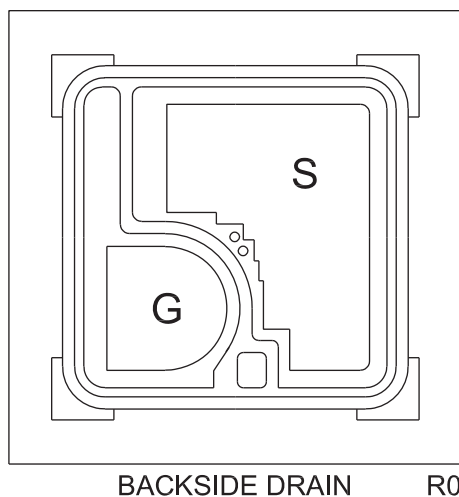
PROCESS CP359R
Small Signal MOSFET
N-Channel Enhancement-Mode MOSFET Chip



PROCESS DETAILS

Die Size	9.1 x 9.1 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	2.5 MILS DIAMETER
Source Bonding Pad Area	3.9 x 3.9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER
290,000

PRINCIPAL DEVICE TYPE
CMRDM3590

R0 (13-May 2010)

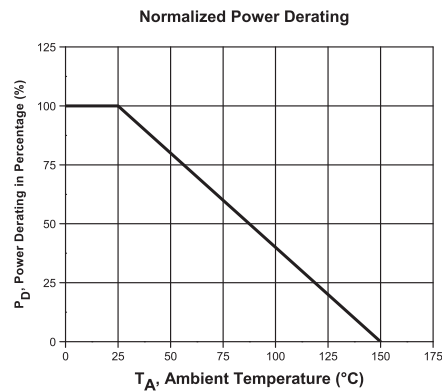
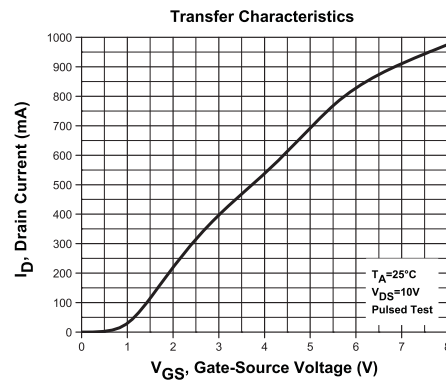
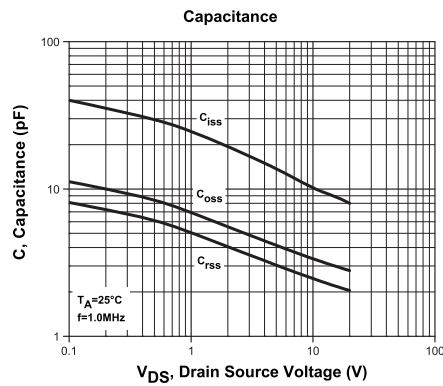
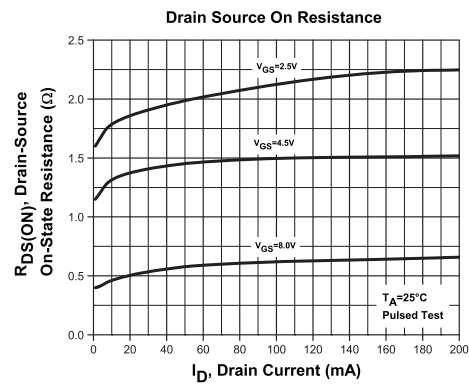
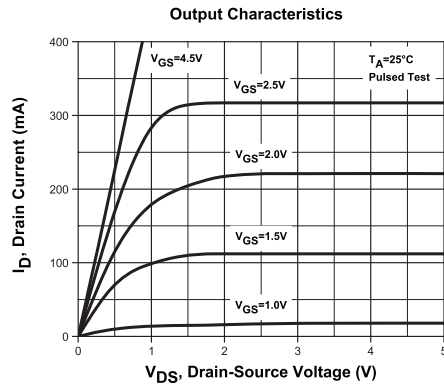
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PROCESS CP359R

Typical Electrical Characteristics



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